

REMARKS

Claims 18, 26, 31-34, 36, 37, 39, 40, and 45 are amended and new Claims 46-49 are added with this submission. The amendments and the new Claims are supported by the present application as filed. No new matter has been added.

In particular, the addition of "zirconium oxide" and "a material containing lead oxide" to Claim 18 is supported by the incorporation by reference of U.S. patent application serial number 09/660,317 at page 12, line 12 of the present application. Application 09/660,317 discloses lenses bonded to light-emitting diodes. The lenses may be Fresnel lenses and may be formed from materials including zirconium oxide and Schott glass SF59. Schott glass SF59 includes lead oxide, as is shown in the material data safety sheet for Schott glass SF59 attached below as Appendix B.

If the Examiner would like to discuss any aspect of this application, the Examiner is invited to telephone the undersigned at (408) 453-9200).

EXPRESS MAIL LABEL NO:

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Respectfully submitted,

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Appendix A

The following identifies the changes that the present submission makes to Claims 18, 26, 31-34, 36, 37, 39, 40, and 45 of U.S. Patent Application Serial No. 09/823,841 (M-8633-1P US).

18. (Amended) The device of claim 12 wherein said [light-emitting diode] semiconductor light emitter comprises a III-nitride semiconductor alloy and said first optical element comprises one of silicon carbide, zinc sulfide, zirconium oxide, a material containing lead oxide, and sapphire.

26. (Amended) The device of claim 25 wherein at least one of said first [Fresnel lens] optical element and said second [Fresnel lens] optical element is designed to focus light.

31. (Amended) The method of claim 27, wherein said [pressing] stamping is executed at an elevated temperature, said elevated temperature being higher than room temperature.

32. (Amended) The method of claim 31, further comprising lowering said elevated temperature to facilitate the separation of [said] a stamping block from said semiconductor light emitter after said [pressing] stamping.

33. (Amended) The method of claim 32, wherein said elevated temperature is higher than the ductile transition temperature of the material constituting said at least one surface on which said [Fresnel lens] optical element is formed.

34. (Amended) A light emitting device comprising:
a semiconductor light emitter; and
at least one optical element stamped on at least one surface of said semiconductor light emitter, wherein said optical element is a first optical element.

36. (Amended) The device of claim 34 wherein said [light-emitting] semiconductor light emitter and said first optical element comprise $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$ where $0 \leq x \leq 1$ and $0 \leq y \leq 1$.

37. (Amended) The device of claim 34 wherein said semiconductor light emitter comprises a III-nitride semiconductor alloy and said first optical element comprises one of silicon carbide, zinc sulfide, and sapphire.

39. (Amended) The device of claim 34 wherein said [light emitting diode] semiconductor light emitter has a flip-chip configuration.

40. (Amended) The device of claim 34 wherein said [light emitting diode] semiconductor light emitter has a configuration in which [the] a light emitting layer of said [light emitting diode] semiconductor light emitter is substantially perpendicular to said [Fresnel lens] first optical element.

45. (Amended) A method for forming a light emitting device, said method comprising:
stamping an optical element in a material, said material being transparent to light emitted from said light emitting device; and
bonding said [optical element] material to a semiconductor light emitter.